

In the Claims:

1. (Currently amended) A semiconductor component having a thin-film semiconductor body (2) arranged on a carrier (4),

~~characterized in that wherein~~

the carrier (4) contains germanium.

2. (Currently amended) The semiconductor component as claimed in claim 1,

~~characterized in that wherein~~

the thin-film semiconductor body (2) is soldered onto the carrier (4).

3. (Currently amended) The semiconductor component as claimed in claim 1 ~~or 2~~,

~~characterized in that wherein~~

the thin-film semiconductor body (2) is soldered onto the carrier (4) by means of a gold-containing solder.

4. (Currently amended) The semiconductor component as claimed in ~~claim 1 one of~~
~~claims 1 to 3,~~

~~characterized in that wherein~~

the thin-film semiconductor body (2) comprises a plurality of individual layers.

5. (Currently amended) The semiconductor component as claimed in claim 1 one of
~~claims 1 to 4,~~

characterized in that wherein

the thin-film semiconductor body (2) or at least one of the individual layers contains a III-V compound semiconductor.

6. (Currently amended) The semiconductor component as claimed in claim 5,

characterized in that wherein

the thin-film semiconductor body (2) or at least one of the individual layers contains $\text{In}_x\text{Al}_y\text{Ga}_{1-x-y}\text{P}$, $0 \leq x \leq 1$, $0 \leq y \leq 1$, $0 \leq x + y \leq 1$.

7. (Currently amended) The semiconductor component as claimed in claim 5,

characterized in that wherein

the thin-film semiconductor (2) or at least one of the individual layers contains $\text{In}_x\text{As}_y\text{Ga}_{1-x-y}\text{P}$, $0 \leq x \leq 1$, $0 \leq y \leq 1$, $0 \leq x + y \leq 1$.

8. (Currently amended) The semiconductor component as claimed in claim 5,

characterized in that wherein

the thin-film semiconductor body (2) or at least one of the individual layers contains $\text{In}_x\text{Al}_y\text{Ga}_{1-x-y}\text{As}_s$ where $0 \leq x \leq 1$, $0 \leq y \leq 1$, $0 \leq x + y \leq 1$ or $\text{In}_x\text{Ga}_{1-x}\text{As}_{1-y}\text{N}_y$ where $0 \leq x \leq 1$, $0 \leq y \leq 1$.

9. (Currently amended) The semiconductor component as claimed in claim 5,

~~characterized in that wherein~~

the thin-film semiconductor body (2) or at least one of the individual layers contains a nitride compound semiconductor, in particular $\text{In}_x\text{Al}_y\text{Ga}_{1-x-y}\text{N}$, $0 \leq x \leq 1$, $0 \leq y \leq 1$, $0 \leq x + y \leq 1$.

10. (Currently amended) The semiconductor component as claimed in claim 1 one of

~~claims 1 to 9,~~

~~characterized in that wherein~~

the thin-film semiconductor body (2) has a radiation-emitting active region.

11. (Currently amended) The semiconductor component as claimed in claim 1 one of
~~claims 1 to 10,~~

~~characterized in that wherein~~

a mirror layer, preferably a metallic mirror layer, is arranged between the thin-film semiconductor body (2) and the carrier (4).

12. (Currently amended) The semiconductor component as claimed in claim 11,

~~characterized in that wherein~~

a dielectric layer is at least partially arranged between the thin-film semiconductor body (2) and the mirror layer.

13. (Currently amended) A method for producing a semiconductor component having a thin-film conductor body (2) arranged on a carrier (4), having the steps of

- a) growing the thin-film semiconductor body on a substrate,
- b) applying the carrier (4) to a side of the thin-film semiconductor body (2) that is remote from the substrate (1), and

c) stripping the thin-film semiconductor body (2) from the substrate,

characterized in that wherein

the carrier (4) contains germanium.

14. (Currently amended) The method as claimed in claim 13,

characterized in that wherein

the substrate is eroded, in particular ground away and/or etched away, in step c).

15. (Currently amended) The method as claimed in claim 13,

characterized in that wherein

the semiconductor body is stripped from the substrate (1) by laser irradiation in step c).

16. (Currently amended) The method as claimed in claim 13 one of claims 13 to 15,

characterized in that wherein

the carrier is soldered on in step b).

17. (Currently amended) The method as claimed in claim 13 one of claims 13 to 16,
characterized in that wherein

a gold layer (3, 3a, 3b) is arranged on that side of the thin-film semiconductor body (2) which faces the carrier and/or on that side of the carrier which faces the thin-film semiconductor body (2), ~~which and wherein said~~ gold layer, when the carrier is soldered on in step b), at least partially forms a melt containing gold and germanium.

18. (Currently amended) The method as claimed in claim 13 one of claims 13 to 17,
characterized in that wherein

prior to step b), a layer containing gold and germanium is applied on that side of the thin-film semiconductor body (2) which faces the carrier and/or on that side of the carrier which faces the thin-film semiconductor body (2).

19. (Currently amended) The method as claimed in claim 13 one of claims 13 to 18,
characterized in that for producing a semiconductor component having a thin-film body
arranged on a carrier that contains germanium, as claimed in one of claims 1 to 12 is produced
by said method.

20. (Currently amended) The semiconductor component as claimed in claim 1, wherein
one of claims 1 to 12 or the method as claimed in one of claims 13 to 19, characterized in that the
semiconductor component is a luminescence diode, in particular a light emitting diode or a laser
diode.

21. (New) The semiconductor component as claimed in claim 20, wherein the semiconductor component is a light emitting diode or a laser diode.

22. (New) The method as claimed in claim 13, wherein the semiconductor component is a luminescence diode.

23. (New) The method as claimed in claim 22, wherein the semiconductor component is a light-emitting diode or a laser diode.